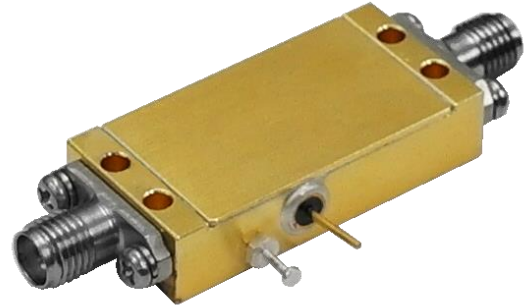


FEATURES:

Linear GaAsFET low noise hybrid design
 Instantaneous full X- Band coverage
 Suitable for all single channel composite modulation standards
 Designed for Radios, Radar, Telecomm, Satellite, Military, Space, MW links
 Also suitable for general lab, commercial & Mil applications
 Built-in regulator, sequencing, and protection circuits
 High efficiency, reliability, and ruggedness


ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification		Notes
Part Number	LNA5006	LNA5006-1	
Operating Frequency Range	8.0 - 12 GHz		
Linear Gain – Small signal	28 dB Min	18 dB Min	
Gain Flatness	2 dB p-p Max		
Output power @ Psat	+13 dBm Min		
Output Power @ P1dB	+13 dBm Min		
Noise Figure	2.2 dB Typ		
Input / output VSWR	2 : 1 Max		
Harmonics	<-30 dBc Typ		
Operating Voltage	12 VDC Nom		11 - 13 VDC range
Current Consumption	200 mA Max	150 mA	
Input Power Protection	+17 dBm Max		

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions (L x W x H)	34.55 x 16.76 x 7.62 mm	
Connectors Input / Output	SMA Female	
Weight	15 gr.	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-40°C to 85 °C	
Storage Temperature Range	-55°C to +85 °C	Non-operating
Shock and Vibration	MIL-STD-810F	Designed to meet

OUTLINE DRAWING

